ACGI085096-P39

X-band matched GaAs Device

Features:

Frequency: 8.5~9.6GHz

Saturated Output Power : P_{Sat}≥39dBm

PowerGain: Gain≥7dB

Add-Efficiency: PAE=30%(type)

Port matching: Zin/Zout=50Ω

Description:

ACGI085096-P39 is an internal matching GaAs device, which adopts advanced co-planar internal matching MCM and thin film circuit technology. The typical working frequency range is 8.5~9.6GHz. This device can be used in different RF/Microwave system and subsystem. The high output power level, high efficiency and wide operating temperature range can make application very flexible.

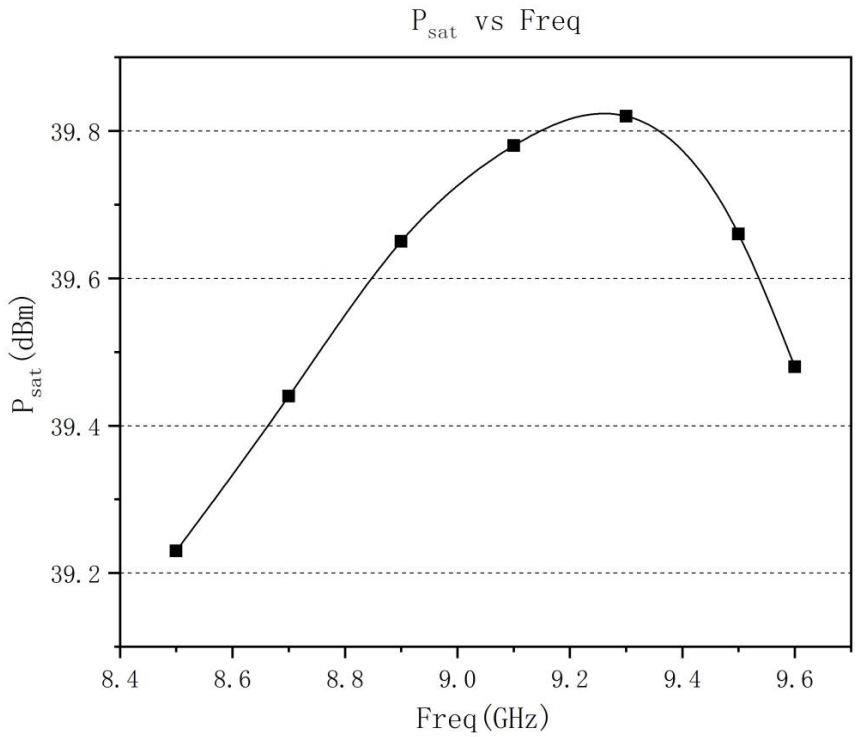
Maximun Ratings (TC=25℃, Not recommended working under this condition):

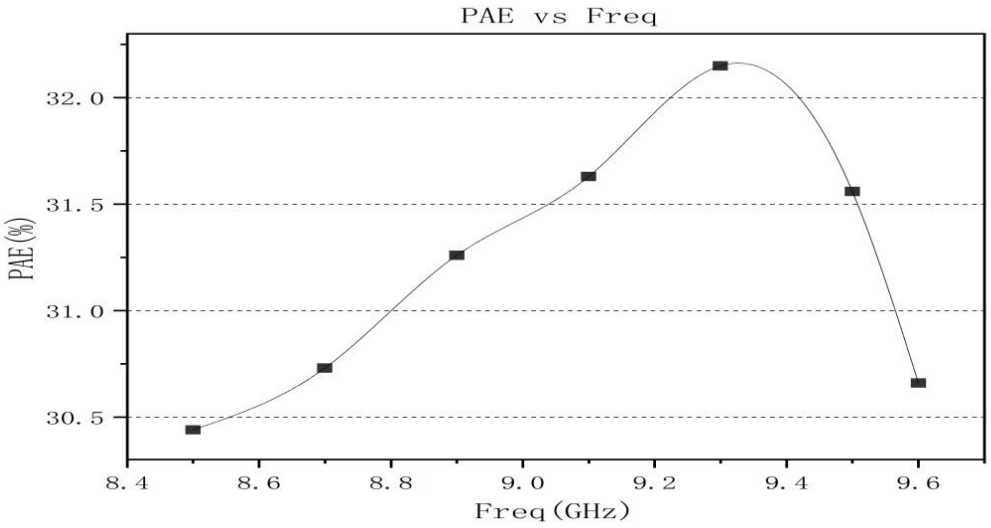
	Symbol	Value	Unit
Voltage between source and drain	V_{ds}	11	V
Voltage between gate and source	V_{gs}	-3	V
Storage Temperature Range	T_{stg}	-65 to +150	℃
Drain and Source Channel Temperature	T_{ch}	150	℃

Electrical Characteristics:

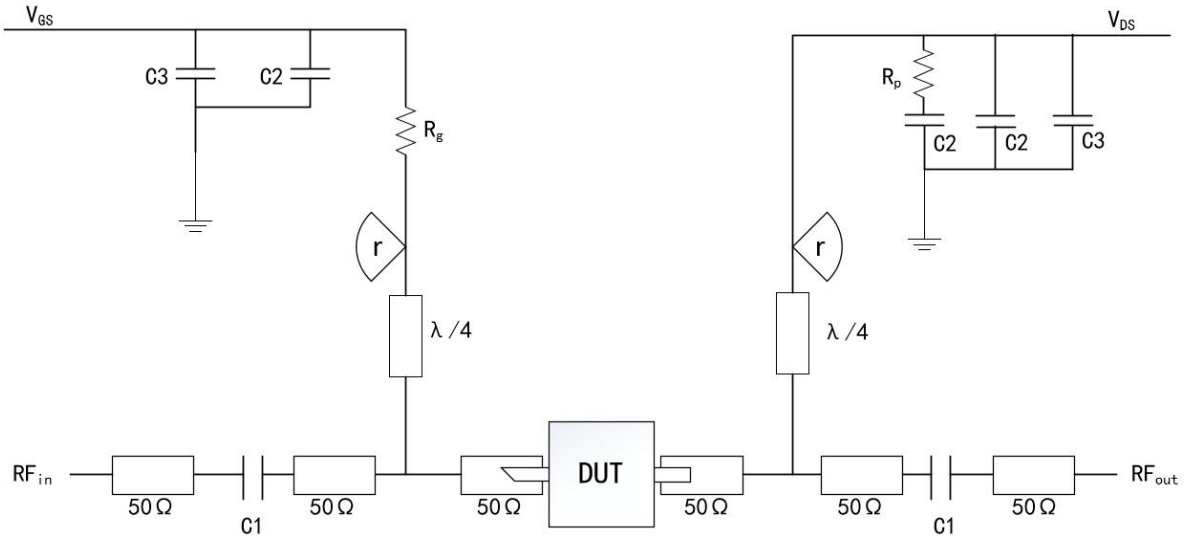
	Symbol	Test condition	Value			Unit
			Min	Typ	Max	
Drain Current	Idsr	Vds=10V CW. Pin: 32dBm Freq: 8.5~9.6GHz	-	2.2	-	A
Saturated output power	Psat		39	-	-	dBm
Gain	Gp		7	-	-	dB
Add-Efficiency	PAE		-	30	-	%
Gain Flatness	ΔG		-0.8	-	+0.8	dB

Typical Curve:





Application Circuit:



DUT：Device to be tested

C1:1pF

C2:1000pF

C3:100uF

Rp:51Ω

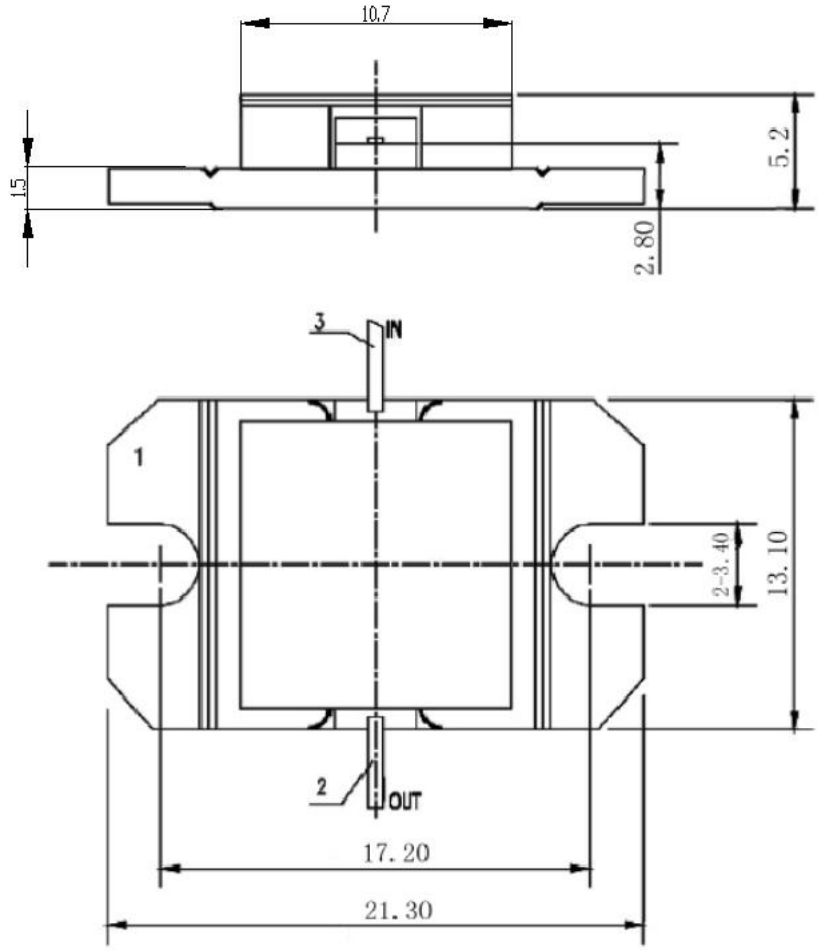
Rg:15Ω

r(radius)≈3.5mm(Rogers5880, 20mil)

ESD Level:

ESD	Class III	2000V

Outline:



Precautions for use:

- Pay attention to drying transportation and storage.
- Pay attention to anti-static during chip use and assembly，and wear grounding anti-static bracelet.
- When powering up，first apply grid power then add leakage.